

General Description

The WSF50N10 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF50N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

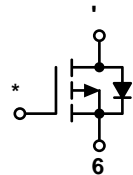
Product Summary

BV_{DSS}	R_{DSON}	I_D
100V	22m Ω	50A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

TO25 2/3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.7	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.3	A
I_{DM}	Pulsed Drain Current ²	160	A
EAS	Single Pulse Avalanche Energy ³	81	mJ
I_{AS}	Avalanche Current	18	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	83	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	33	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.5	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	22	28	mΩ
		V _{GS} =4.5V, I _D =15A	---	24	32	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	2.0	3.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.52	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	10	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	25.7	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.0	1.2	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =30V, V _{GS} =10V, I _D =20A	---	50	65	nC
Q _{gs}	Gate-Source Charge		---	8	14	
Q _{gd}	Gate-Drain Charge		---	10	18	
T _{d(on)}	Turn-On Delay Time		---	18	33	
T _r	Rise Time	V _{DD} =30V, V _{GS} =10V, I _D =20A	---	9	17	ns
T _{d(off)}	Turn-Off Delay Time		---	56	101	
T _f	Fall Time		---	14	26	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	2450	3180	pF
C _{oss}	Output Capacitance		---	150	192	
C _{riss}	Reverse Transfer Capacitance		---	85	115	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.1mH, I _{AS} =18A	80	---	---	mJ

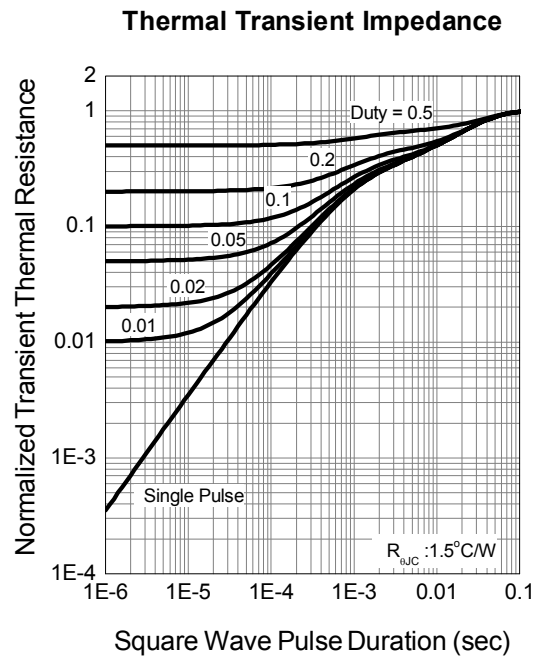
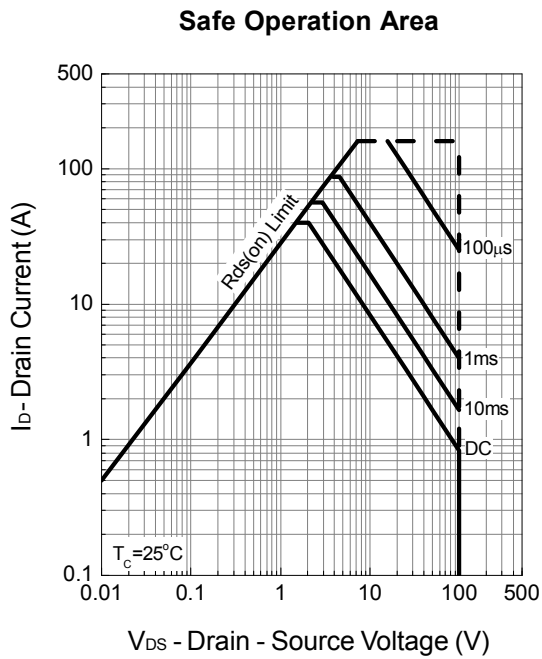
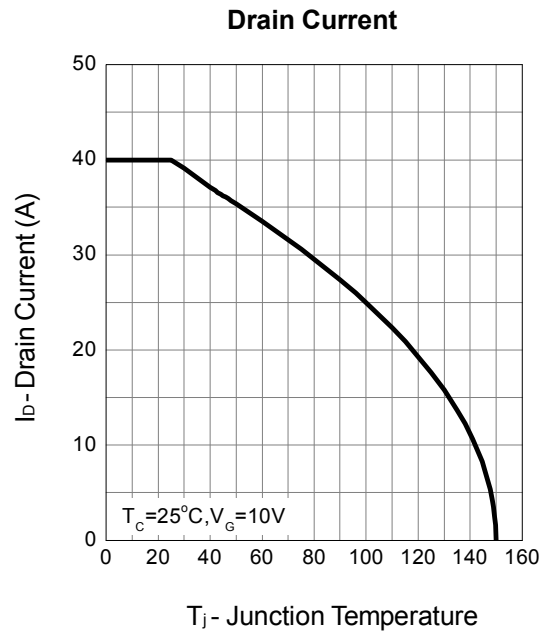
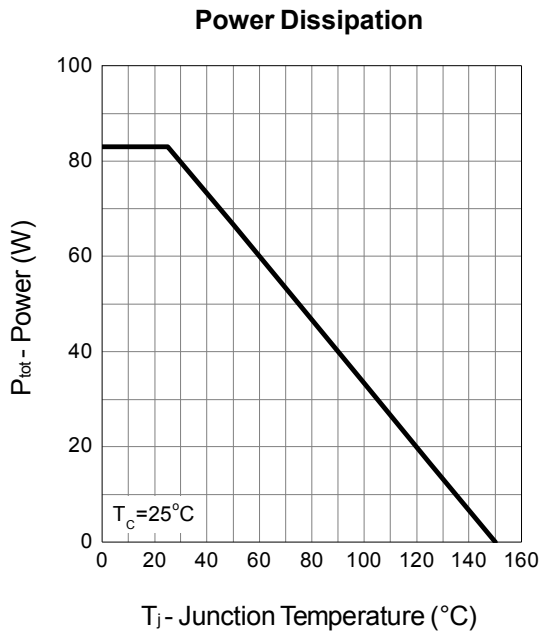
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	20	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	45	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =20A, T _J =25°C	---	---	1.3	V
t _{rr}	Reverse Recovery Time	I _F =20A, dI/dt=100A/μs, T _J =25°C	---	40	---	nS
Q _{rr}	Reverse Recovery Charge		---	83	---	nC

Note :

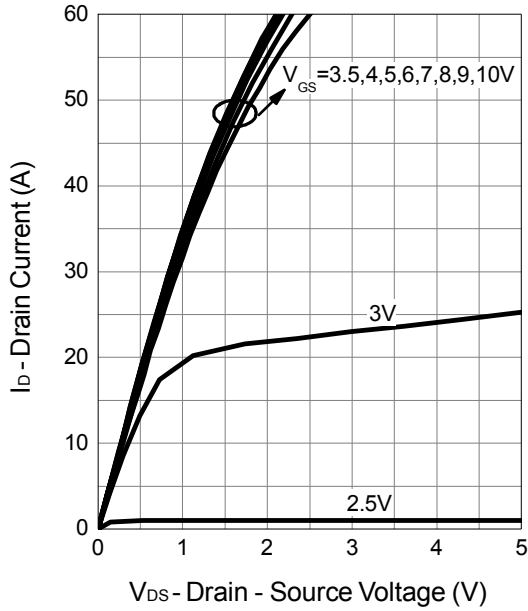
- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=18A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

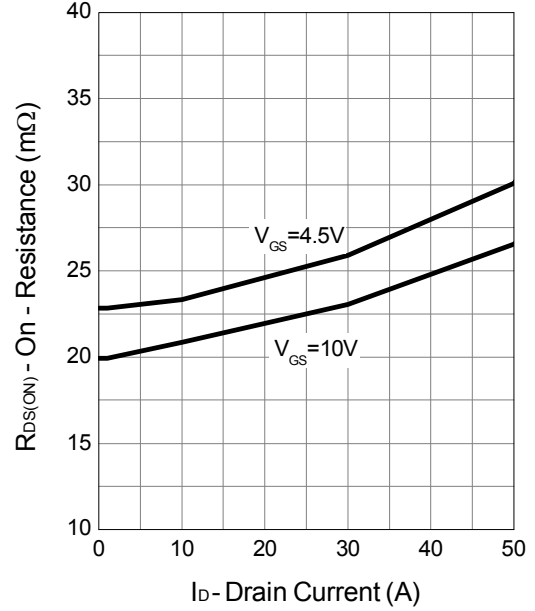


Typical Characteristics

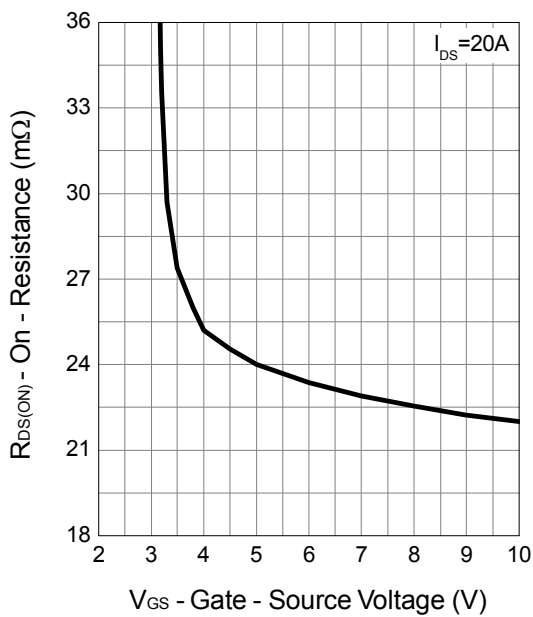
Output Characteristics



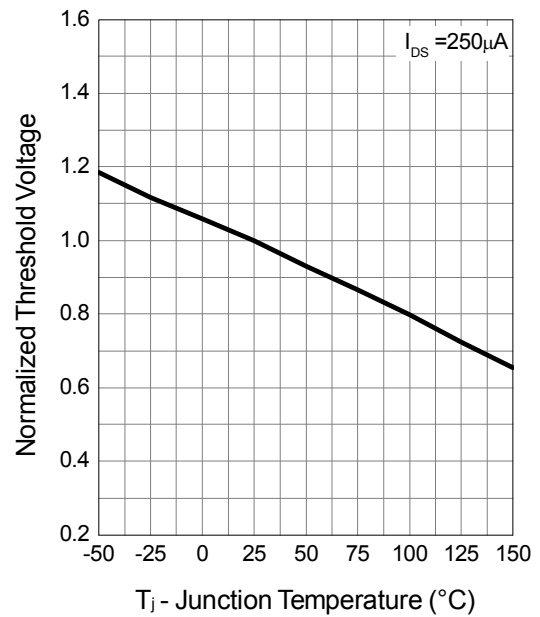
Drain-Source On Resistance



Gate-Source On Resistance

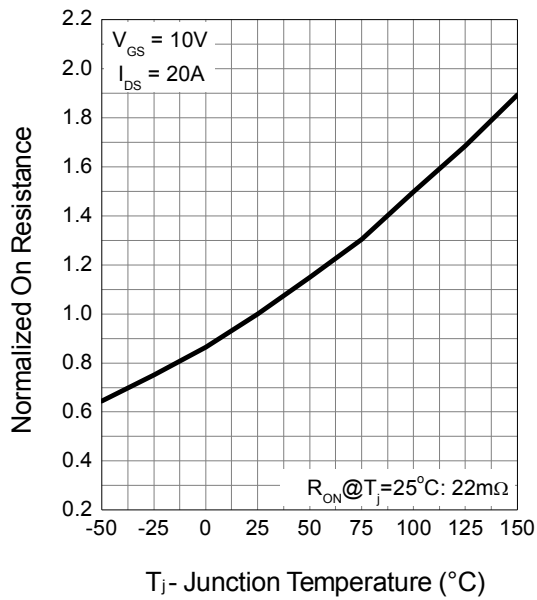


Gate Threshold Voltage

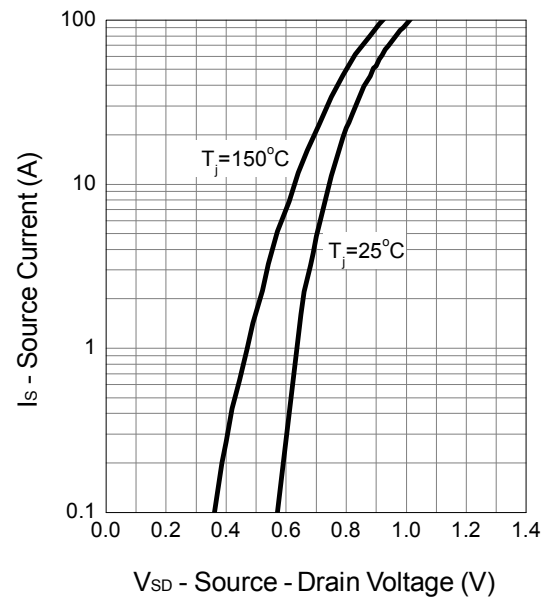


Typical Characteristics

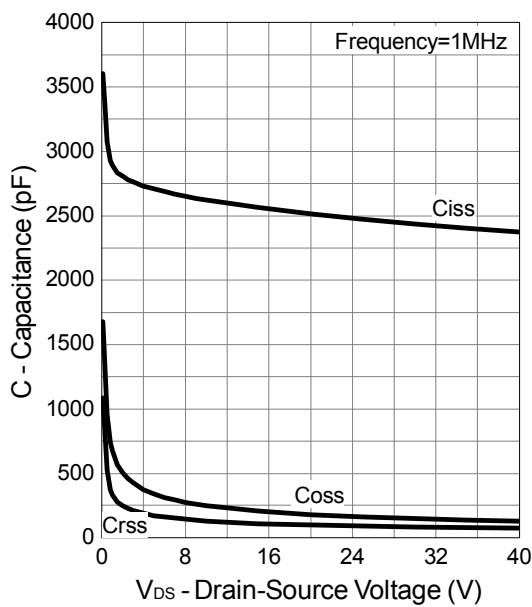
Drain-Source On Resistance



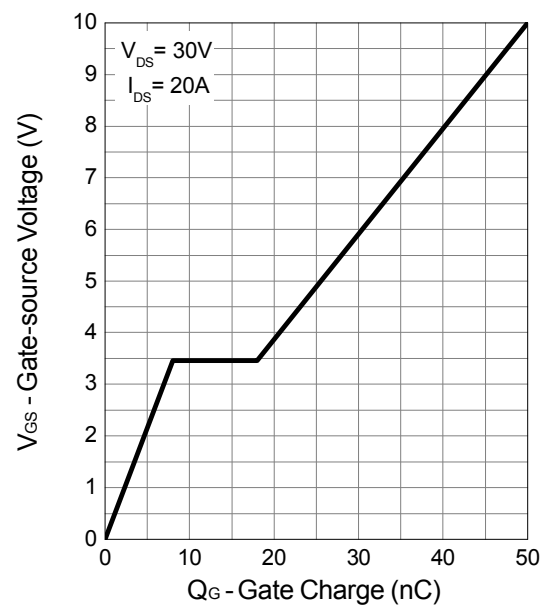
Source-Drain Diode Forward



Capacitance



Gate Charge





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